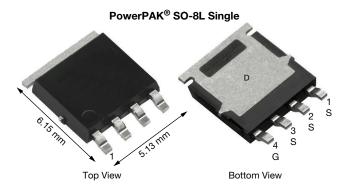
SQJ414EP

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Vishay Siliconix

Automotive N-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	30			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0120			
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0170			
I _D (A)	30			
Configuration	Single			
Package	PowerPAK SO-8L			

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

N-Channel MOSFET

D

S



COMPLIANT HALOGEN

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	30	V	
Gate-source voltage		V _{GS}	± 20	v	
Continuous drain current	$T_C = 25 \ ^\circ C \ ^a$	- I _D	30		
	T _C = 125 °C		25		
Continuous source current (diode conduction) ^a		I _S	30	А	
Pulsed drain current ^b		I _{DM}	90		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	22		
Single pulse avalanche energy		E _{AS}	24.2	mJ	
Maximum power dissipation ^b	T _C = 25 °C	PD	45	W	
	T _C = 125 °C	гD	15	vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	70	°C/W
Junction-to-case (drain)		R _{thJC}	3.3	C/ W

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		•		•				
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		30	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		2.0	2.5		
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 30 V	-	-	1		
		$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	250		
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	15	-	-	А	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}$	I _D = 4.5 A	-	0.0098	0.0120	Ω	
		$V_{GS} = 4.5 V$	I _D = 3 A	-	0.0139	0.0170		
		$V_{GS} = 10 V$	I _D = 4.5 A, T _J = 125 °C	-	-	0.0188		
		$V_{GS} = 10 \text{ V}$	I _D = 4.5 A, T _J = 175 °C	-	-	0.0227		
Forward transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 4 A	-	31	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{DS} = 15 V, f = 1 MHz	-	850	1110	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	167	220		
Reverse transfer capacitance	C _{rss}			-	60	80		
Total gate charge ^c	Qg		V _{DS} = 15 V, I _D = 5 A	-	15	25	nC	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 V$		-	3	-		
Gate-drain charge ^c	Q _{gd}				3	-	1	
Gate resistance	Rg	f = 1 MHz		0.7	1.5	2.3	Ω	
Turn-on delay time ^c	t _{d(on)}	$V_{DD} = 15 \text{ V}, \text{ R}_{\text{L}} = 3.8 \Omega$ $\text{I}_{\text{D}} \cong 4 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		-	11	20	ns	
Rise time ^c	t _r			-	5	10		
Turn-off delay time ^c	t _{d(off)}			-	21	40		
Fall time ^c	t _f			-	5	10		
Source-Drain Diode Ratings and Charac	cteristics ^b	•			•			
Pulsed current ^a	I _{SM}			-	-	90	Α	
Forward voltage	V _{SD}	$I_{F} = 4 \text{ A}, V_{GS} = 0$		-	0.79	1.2	V	
Body diode reverse recovery time	t _{rr}	I _F = 3 A, di/dt = 100 A/μs		-	22	50	ns	
Body diode reverse recovery charge	Q _{rr}			-	18	40	nC	
Reverse recovery fall time	ta			-	14	-	ns	
Reverse recovery rise time	t _b			-	8	-		
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.5	-	Α	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

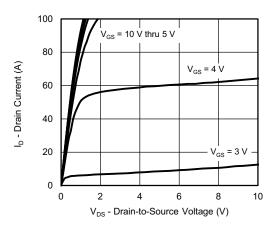
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

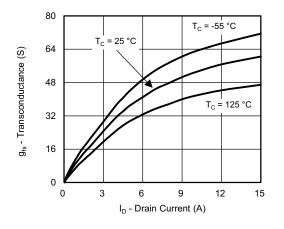
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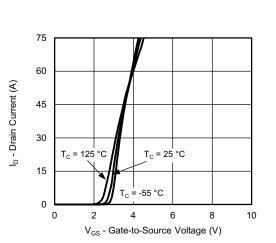
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



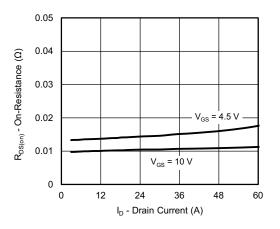
Output Characteristics



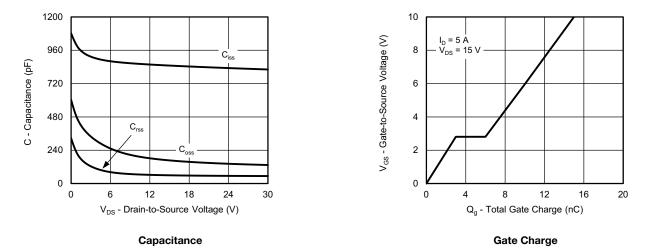
Transconductance



Transfer Characteristics



On-Resistance vs. Drain Current



S17-0520-Rev. A, 10-Apr-17

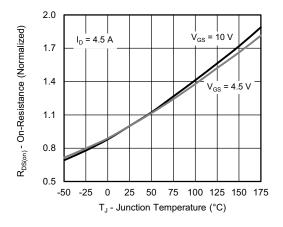
3

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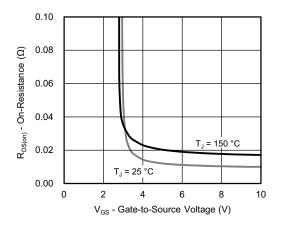
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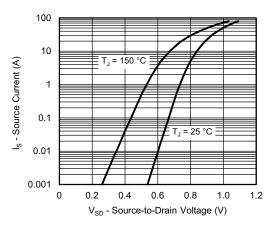
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



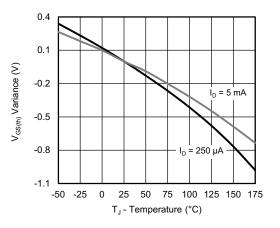
On-Resistance vs. Junction Temperature

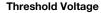


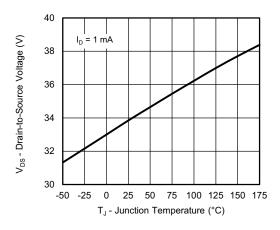
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







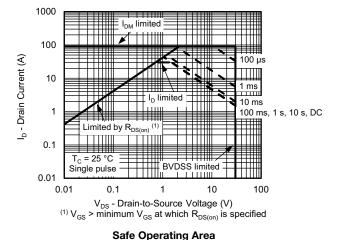
Drain Source Breakdown vs. Junction Temperature

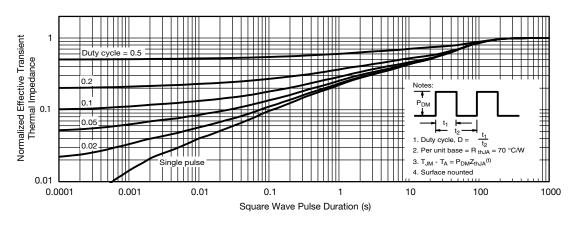
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



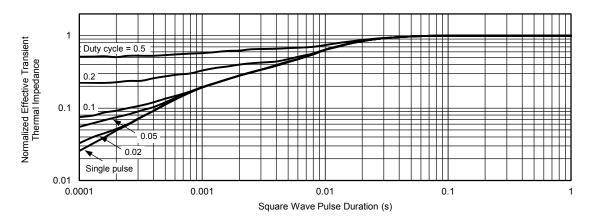


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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